Title: "Semiconductor Heterostructures Having Reduced Dislocation Pile-Ups and Related Methods" Inventors: Weshoff et al. Serial No. 10/646,353 Aty Docker No. ASC-058B Agent: Matthew T. Currie Replacement Sheet I of 6

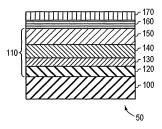


FIG. 1

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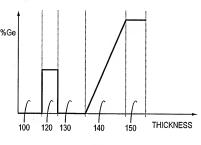


FIG. 2

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	QUALITATIVE EVALUATION OF DISLOCATION PILE-UP DENSITY			
% Ge	H* = 0.6 T _{crit}	H = 1.25 T _{crit}	H = 2 T _{crit}	H = 5 T _{crit}
5	HIGH	MEDIUM	LOW	LOW
10	HIGH	MEDIUM	MEDIUM	LOW
15	HIGH	MEDIUM	MEDIUM	LOW

 * THICKNESS (H) OF THE SEED LAYER RELATIVE TO ITS CRITICAL THICKNESS (T_{crit}).

FIG. 3

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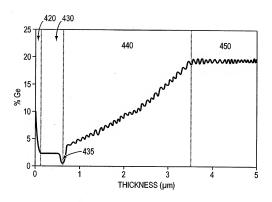


FIG. 4

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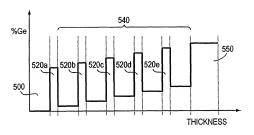


FIG. 5

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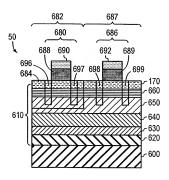


FIG. 6